

N-Channel 16-V (D-S) MOSFET

PRODUCT SUMMARY

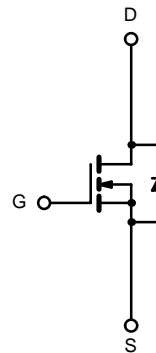
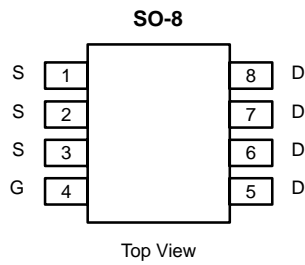
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)
16	0.0033 @ V _{GS} = 4.5 V	25
	0.0055 @ V _{GS} = 2.5 V	20

FEATURES

- TrenchFET® Power MOSFETS: 2.5-V Rated
- Low 3.3-mΩ r_{DS(on)}
- Low Gate Resistance
- 100% R_G Tested

APPLICATIONS

- Synchronous Rectification
- Low Output Voltage Synchronous Rectification



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)

Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V _{DS}	16		V
Gate-Source Voltage		V _{GS}	±8		
Continuous Drain Current (T _J = 150°C) ^a	T _A = 25°C	I _D	25	17	A
	T _A = 70°C		20	13	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	60		
Continuous Source Current (Diode Conduction) ^a		I _S	2.9	1.3	W
Maximum Power Dissipation ^a	T _A = 25°C	P _D	3.5	1.6	
	T _A = 70°C		2.2	1	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 10 sec	R _{thJA}	29	35	°C/W
	Steady State		67	80	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	13	16	

Notes

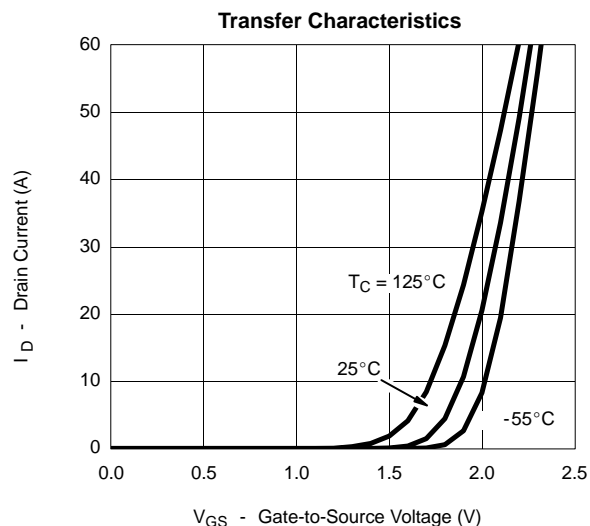
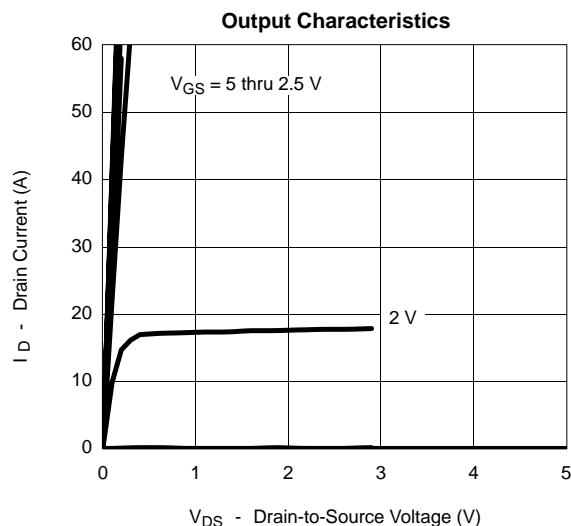
a. Surface Mounted on 1" x 1" FR4 Board.

SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.6			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 12.8 V, V _{GS} = 0 V			1	μA
		V _{DS} = 12.8 V, V _{GS} = 0 V, T _J = 55 °C			5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 4.5 V	30			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 4.5 V, I _D = 25 A		0.0027	0.0033	Ω
		V _{GS} = 2.5 V, I _D = 20 A		0.0045	0.0055	
Forward Transconductance ^a	g _{fs}	V _{DS} = 6 V, I _D = 25 A		140		S
Diode Forward Voltage ^a	V _{SD}	I _S = 2.9 A, V _{GS} = 0 V		0.75	1.1	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = 6 V, V _{GS} = 4.5 V, I _D = 25 A		48	70	nC
Gate-Source Charge	Q _{gs}			11.8		
Gate-Drain Charge	Q _{gd}			8.9		
Gate Resistance	R _g		0.5	1.3	2.2	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 6 V, R _L = 6 Ω I _D ≅ 1 A, V _{GEN} = 4.5 V, R _G = 6 Ω		42	60	ns
Rise Time	t _r			38	60	
Turn-Off Delay Time	t _{d(off)}			120	180	
Fall Time	t _f			50	75	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.9 A, di/dt = 100 A/μs		80	120	

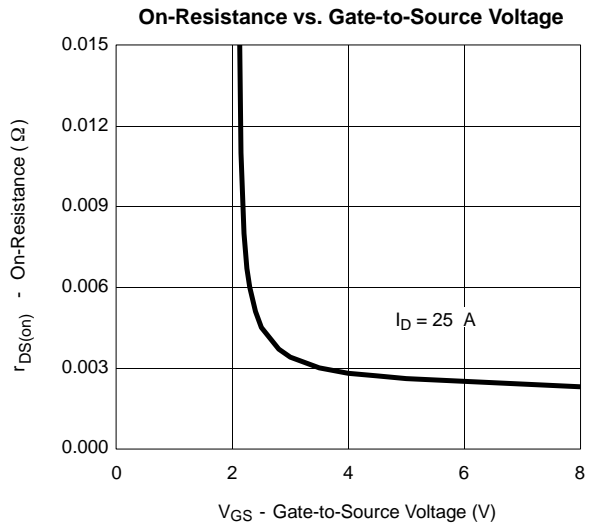
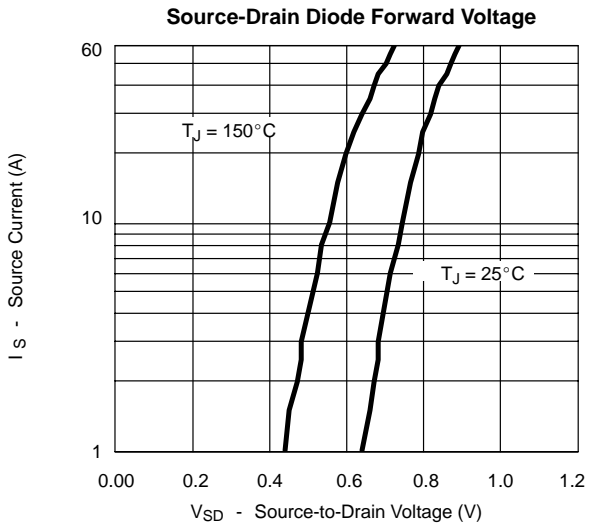
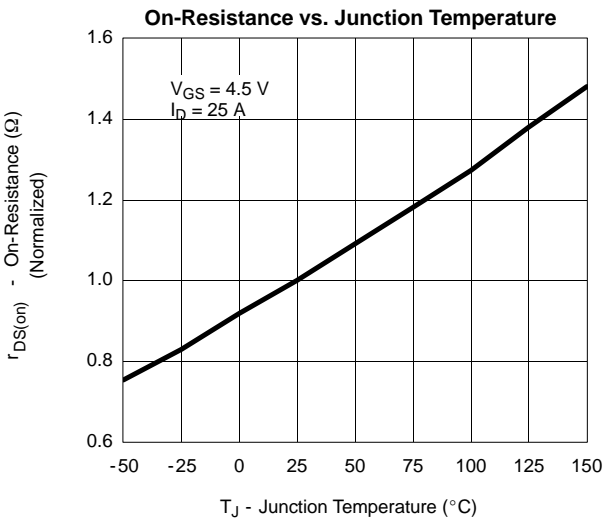
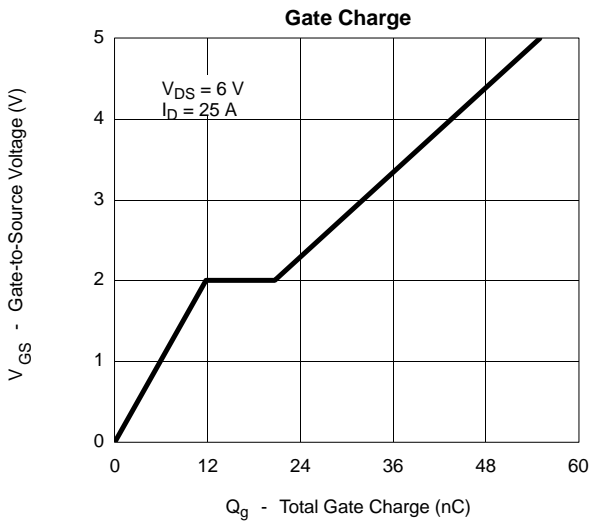
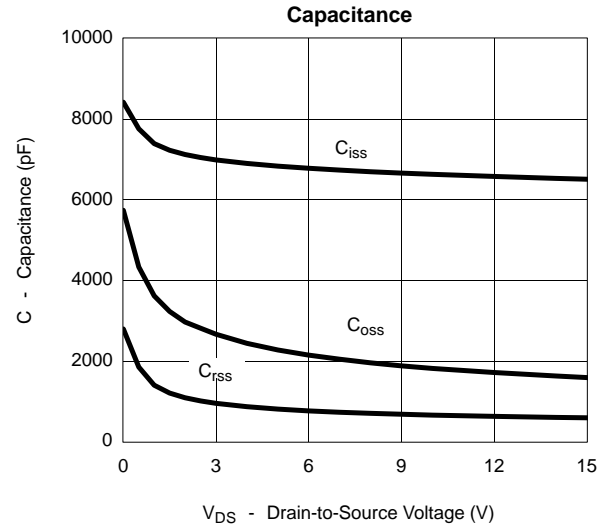
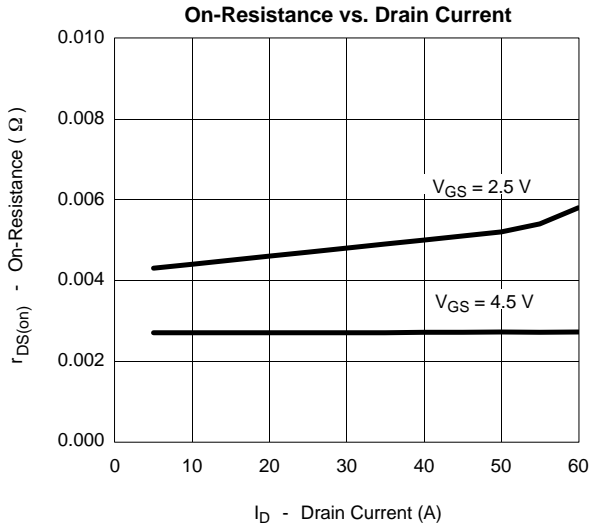
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

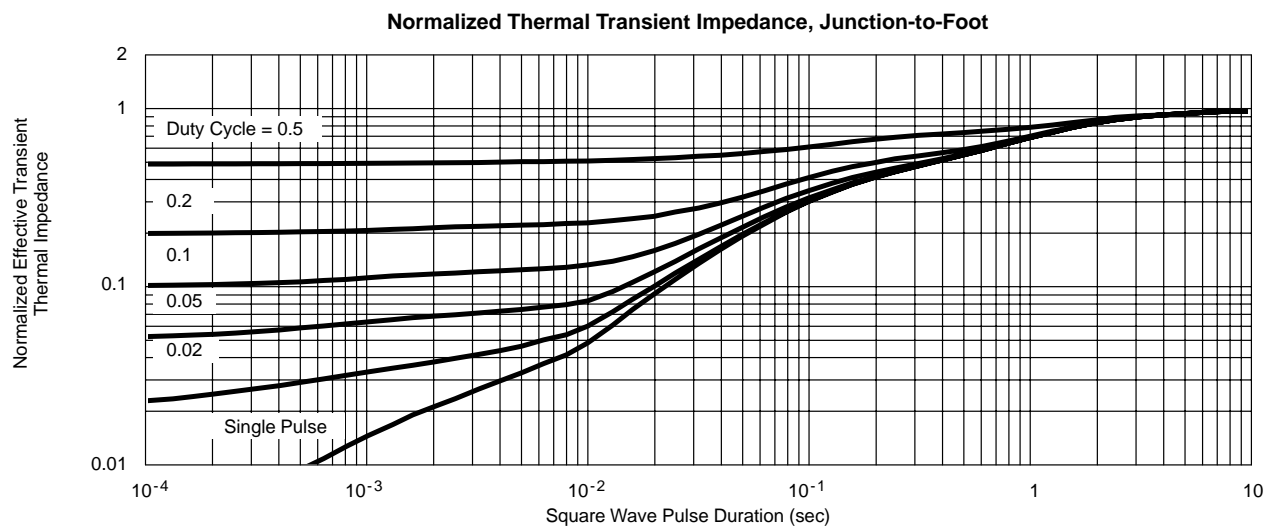
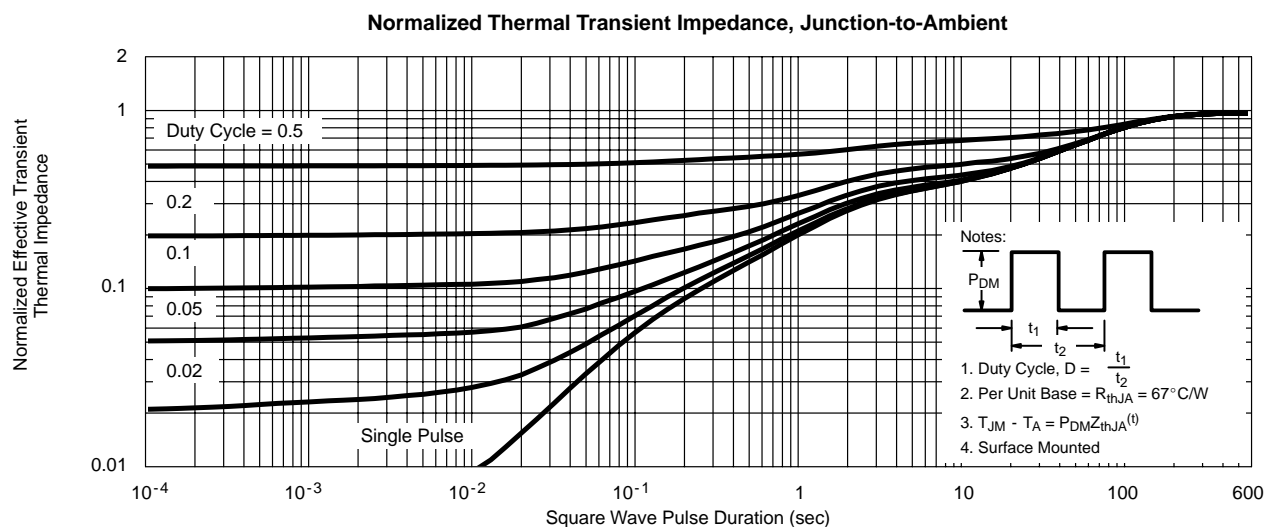
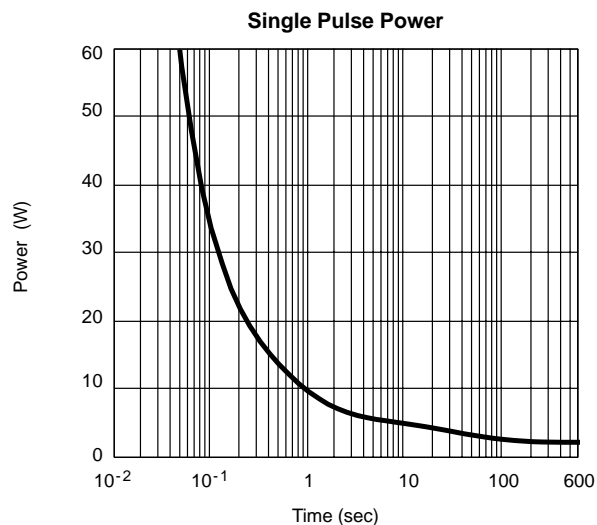
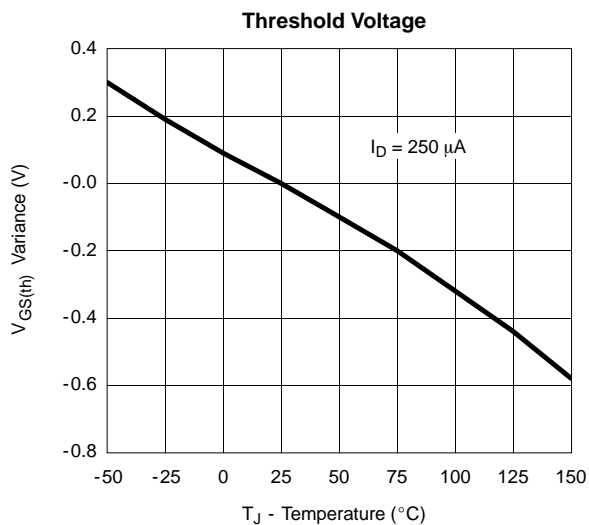
TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



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